

Version With Markings to Show Changes Made

In the Specification, paragraph 10:

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FIG. 1 illustrates a conventionally fabricated semiconductor device 10, which includes a die 12 affixed to a solder mask 18 by an adhesive layer 14. The die 12 has contacts 20 in connection with contacts 22 [on] in the solder mask 18. Specifically, each contact 20 is connected with a respective contact 22 through a wire bond 28. The solder mask 18 is affixed to a printed circuit board 40 or other substrate. The solder mask 18 contains DGMEA or DGME, or other materials. Further, a heavy aromatic naphtha may be used as a photoinitiator.

In the Claims:

1. (Amended) A semiconductor device comprising:
 - a solder mask;
 - a die; andan adhesive layer between said die and said solder mask, wherein said adhesive layer [comprises a material that] remains voidless after outgassing from said solder mask and is at least partially curable at a temperature below about 100°C.

12. (Amended) A semiconductor device comprising:

- a solder mask;
- a die;

electrical contacts [on] in said solder mask and on said die, each said contact on said die being wire bonded to a respective said contact [on] in said mask, said electrical contacts being devoid of contamination caused by outgassing from said solder mask; and an adhesive layer affixing said die to said solder mask, said adhesive layer [comprising a material that is] being curable at a temperature below about 100°C and at a temperature between about 20°C and about 50°C higher than a glassy temperature of said adhesive layer.